



100V N-CHANNEL ENHANCEMENT MODE MOSFET IN SOT23 PACKAGE

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C (Note 6)
100V	700mΩ @ V _{GS} = 10 V	0.76A
1007	$900\text{m}\Omega$ @ $V_{GS} = 6V$	0.67A

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- · Power Management Functions
- Motor Control
- · Disconnect switches

Features

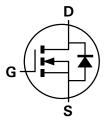
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

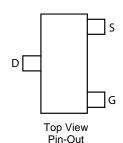
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.008 grams (approximate)







Device Symbol



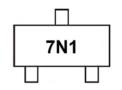
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A07FTA	7N1	7	8	3.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

Marking Information



7N1 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Charact	Symbol	Value	Unit	
Drain-Source Voltage	Drain-Source Voltage				V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current	Steady State	@ V _{GS} = 10V; T _A = +25°C (Note 6) @ V _{GS} = 10V; T _A = +70°C (Note 6) @ V _{GS} = 10V; T _A = +100°C (Note 6) @ V _{GS} = 10V; T _A = +25°C (Note 5)	I _D	0.8 0.6 0.5 0.7	А
Pulsed Drain Current (Note 7)			I _{DM}	3.5	Α
Continuous Source Current (Body Diode) (Note 6)			Is	0.5	Α
Pulsed Source Current (Body Diode) (Note 7)			I _{SM}	3.5	А

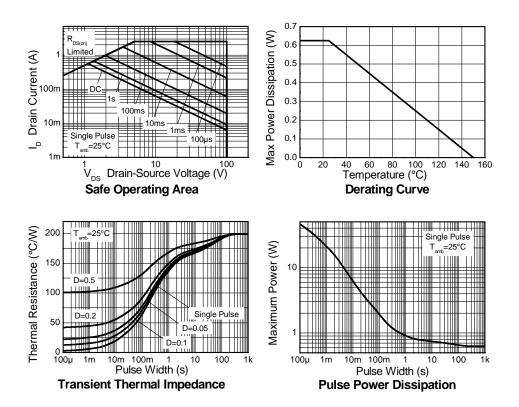
Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	625	mW
Power Dissipation (Note 6)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	$R_{ heta JL}$	194	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

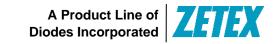
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- To a device surface mounted on FR4 PCB measured at t ≤ 10 sec.
 Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300μs pulse width limited by maximum junction temperature.
 Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

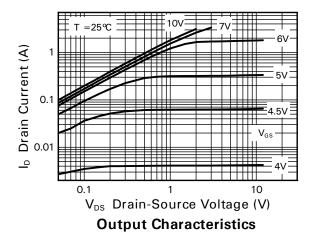
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS		ā.	ā.			_	
Gate Threshold Voltage	V _{GS(th)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain Source On Registence (Note 0)	В		540	700	mΩ	$V_{GS} = 10V, I_D = 1.5A$	
Static Drain-Source On-Resistance (Note 9)	R _{DS} (ON)	_	700	900		$V_{GS} = 6V$, $I_D = 1A$	
Forward Transconductance (Notes 9 & 11)	g fs	_	1.6	_	S	$V_{DS} = 15V, I_{D} = 1A$	
Diodes Forward Voltage (Note 9)	V_{SD}	_	0.85	0.95	V	$T_J = +25$ °C, $I_S = 1.5$ A, $V_{GS} = 0$ V	
DYNAMIC CHARACTERISTICS						_	
Input Capacitance (Notes 10 & 11)	C _{iss}	_	138	280		V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance (Notes 10 & 11)	Coss		12	25	pF		
Reverse Transfer Capacitance (Notes 10 & 11)	C _{rss}		6	12			
Gate Resistance (Notes 10 & 11)	Rg	_	2	4	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge (Notes 10 & 11)	Qg	_	2.9	6		101/11/ 501/	
Gate-Source Charge (Notes 10 & 11)	Q_{gs}	_	0.7	1.5	nC	$V_{GS} = 10V, V_{DS} = 50V,$ $I_{D} = 1A$	
Gate-Drain Charge (Notes 10 & 11)	Q _{gd}	_	1	2			
Reverse Recovery Time (Note 11)	t _{rr}	_	27	60	ns $T_J = +25$ °C, $I_F = 1.8$ A,		
Reverse Recovery Charge (Note 11)	Q _{rr}	_	12	_	nC	di/dt = 100A/µs	
Turn-On Delay Time (Notes 10 & 11)	t _{D(on)}	_	1.8	_			
Turn-On Rise Time (Notes 10 & 11)	t _r	_	1.5	_		$V_{GS} = 10V, V_{DD} = 50V,$ $R_{G} = 6\Omega, I_{D} = 1A$	
Turn-Off Delay Time (Notes 10 & 11)	t _{D(off)}	_	4.1	_	ns		
Turn-Off Fall Time (Notes 10 & 11)	t _f	_	2.1	_			

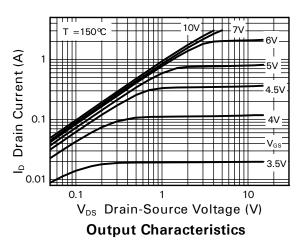
Notes:

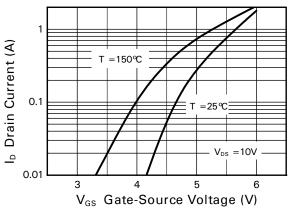
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%. 10. Switching characteristics are independent of operating junction temperature. 11. For design aid only, not subject to production testing.

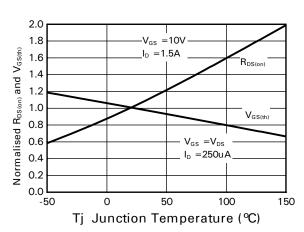


Typical Characteristics



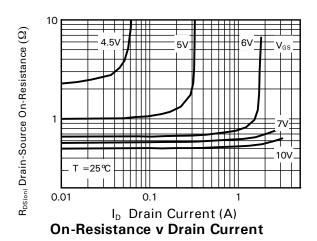


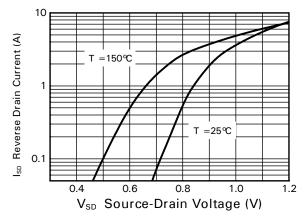




Typical Transfer Characteristics



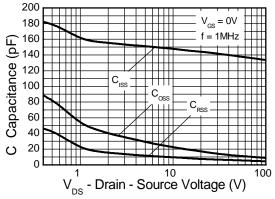


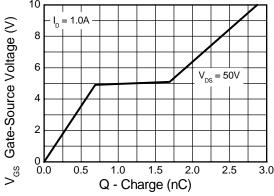


Source-Drain Diode Forward Voltage



Typical Characteristics (cont.)

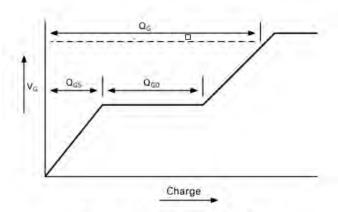




Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge

Test Circuits

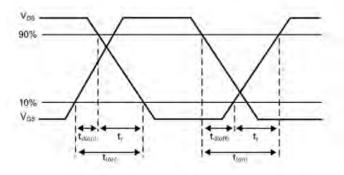


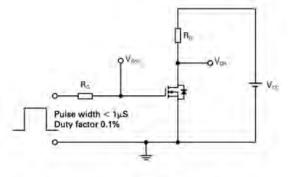
Current regulator

12V 0.2µF 50k Same as D.U.T

Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

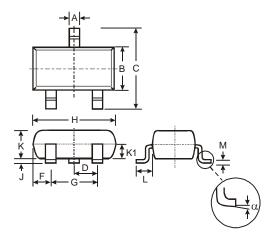
Switching time test circuit





Package Outline Dimensions

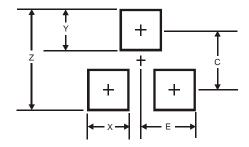
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
C	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Υ	0.9		
С	2.0		
E	1.35		





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